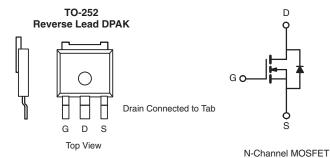


# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0076			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.009			
I <sub>D</sub> (A)	50			
Configuration	Single			



### **FEATURES**

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>q</sub> and UIS Tested
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
Package	TO-252 Reverse Lead DPAK
Lead (Pb)-free and Halogen-free	SQR50N06-07L-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	60		
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	50		
	T <sub>C</sub> = 125 °C		50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	50	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	48		
Single Pulse Avalanche Energy		E <sub>AS</sub>	115	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	136	W	
	T <sub>C</sub> = 125 °C		45	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	1.1	C/VV

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

## **SQR50N06-07L**

# Vishay Siliconix



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•	l .		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0064	0.0076	Ω	
Durin On the Oralla Buristana		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0130		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0160		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 20 A	-	0.0078	0.0090		
Forward Transconductanceb	9fs	V <sub>DS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		82	-	S	
Dynamic <sup>b</sup>					•			
Input Capacitance	C <sub>iss</sub>			-	4455	5570		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	407	510	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	223	280		
Total Gate Charge <sup>c</sup>	Qg			-	80	120		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	11.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1			15.7	-	1	
Gate Resistance	$R_g$	f = 1 MHz		1	2	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	12	18		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_L = 0.6 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	13	20	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	42	63		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		-	0.85	1.5	V	

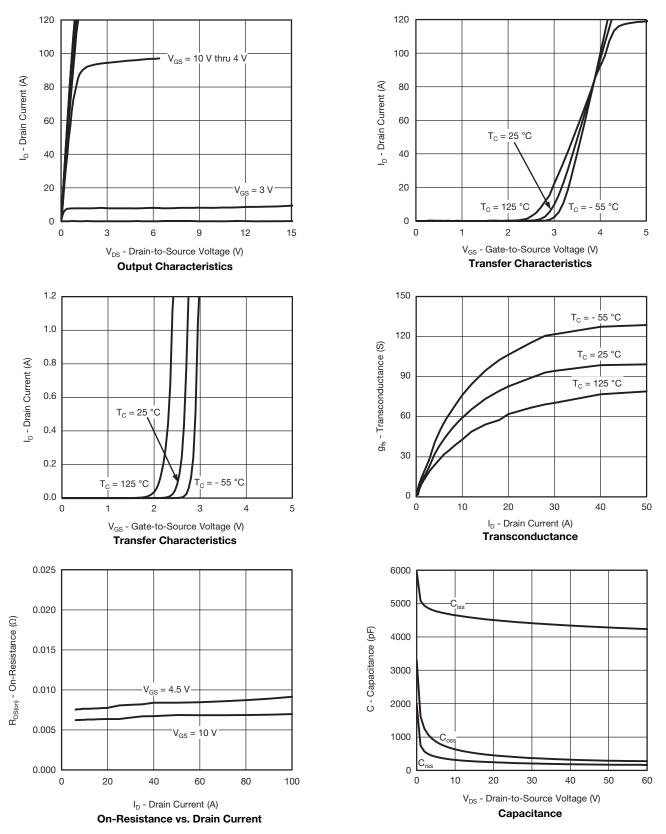
#### **Notes**

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



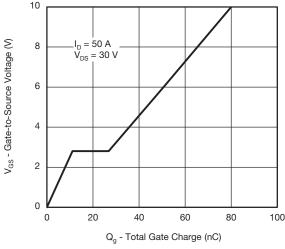
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



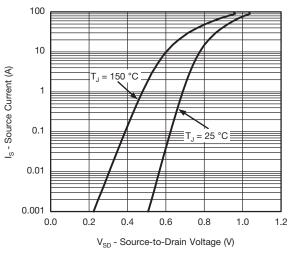
Document Number: 69066 S11-1089-Rev. D, 13-Jun-11



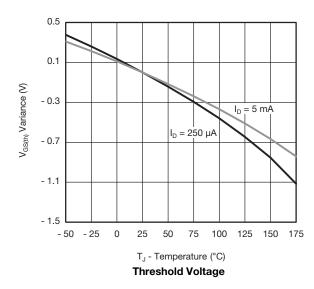
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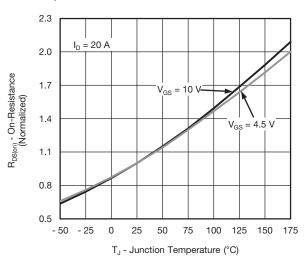


### **Gate Charge**

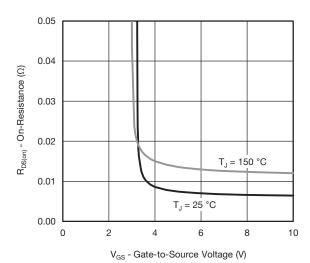


Source Drain Diode Forward Voltage

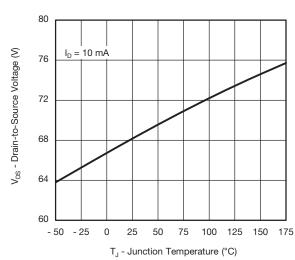




On-Resistance vs. Junction Temperature



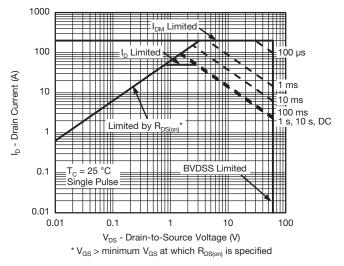
On-Resistance vs. Gate-to-Source Voltage



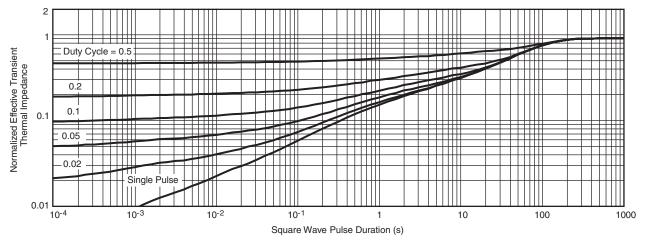
**Drain Source Breakdown vs. Junction Temperature** 



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



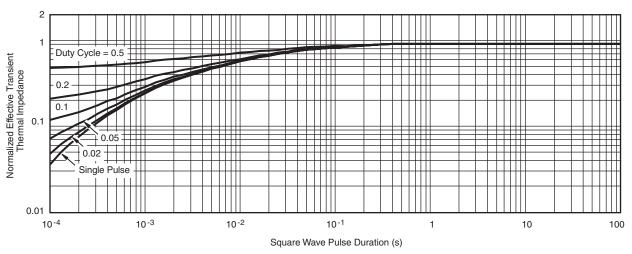
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



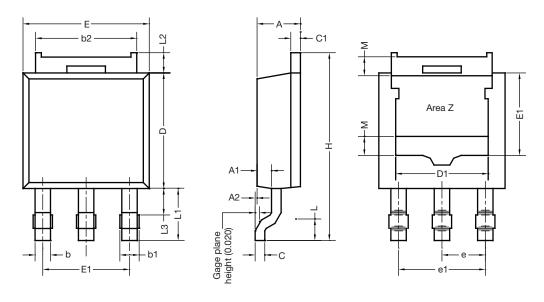
### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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## **TO-252 Reverse Lead Case Outline**



### Notes

- Dimension L3 for reference only
- Area Z: unplated area more than 80 % heatsink area and for partial plating part only

DIM.	MILL	IMETERS	INCHES		
DIN.	MIN.	MAX.	MIN.	MAX.	
A	2.23	2.33	0.088	0.092	
A1	0.64	0.89	0.025	0.035	
A2	0.03	0.18	0.001	0.007	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.49	5.00	0.177	0.197	
E	6.48	6.73	0.255	0.265	
E1	4.32	-	0.170	-	
е	2.28 BSC		0.09	0 BSC	
e1	4.57 BSC		0.18	0 BSC	
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.10	8 BSC	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
М	-	1.00 (reference only)	-	0.039 (reference only)	

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